NSN 5961-00-840-3395

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Thyristor Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-00-840-3395 **Inclosure Material:** Metal **Overall Length:** 1.250 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 1.060 inches **Thread Size:** 0.500 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 600.0 repetitive peak reverse voltage and 3.0 gate trigger voltage, dc and 10.0 forward voltage, peak **Current Rating Per Characteristic:** 55.00 amperes forward current, average megahertz and 35.00 amperes forward current, average and 700.00 amperes forward current, average preset **Power Rating Per Characteristic:** 5.0 watts small-signal input power, common-collector blank **Maximum Operating Tempurature Per Measurement Point:** 125.0 degrees celsius junction **Special Features:** Terminal q type 1 and 2, terminal type, threaded stud and solderless; junction pattern arrangement: pnpn **Thread Series Designator:** Unf **Terminal Type And Quantity:** 2 tab, solder lug and 1 threaded stud Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: